

## 1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors





Product data sheet

## 1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated antiparallel E-C diode in a SOT428 (DPAK) surface mountable plastic package.

## 2. Features and benefits

- Fast switching
- High voltage capability
- Integrated anti-parallel E-C diode
- Surface mountable plastic package
- Very low switching and conduction losses

## 3. Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

### 4. Pinning information

Table 1. Pinning information								
Symbol	Description	Simplified outline	Graphic symbol					
В	base	mb	Ç					
С	collector[1]							
E emitter		B [						
			l E					
			sym131					
		DPAK (SOT428)						
	Symbol B C	SymbolDescriptionBbaseCcollector[1]	SymbolDescriptionSimplified outlineBbasembCcollector[1]Eemitter					

[1] It is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

NPN power transistor with integrated diode

# 5. Ordering information

Table 2. Ordering infor	mation				
Type number	Package				
	Name	Description	Version		
BUJD105AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

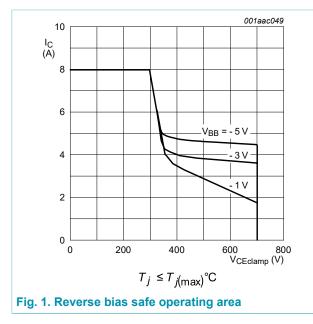
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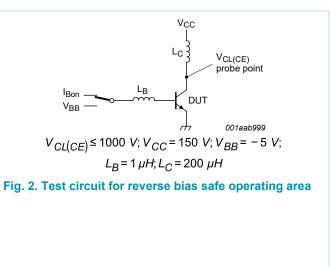
### 6. Limiting values

#### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
V <sub>CBO</sub>	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
I <sub>C</sub>	collector current	DC; <u>Fig. 1; Fig. 2</u>	-	8	А
I <sub>CM</sub>	peak collector current	Fig. 1; Fig. 2	-	16	А
I <sub>B</sub>	base current	DC	-	4	А
I <sub>BM</sub>	peak base current		-	8	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; <u>Fig. 3</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C

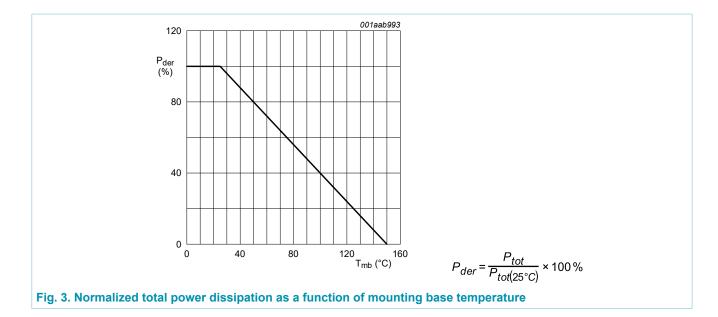




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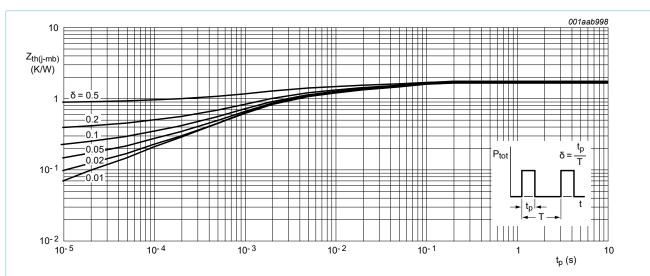


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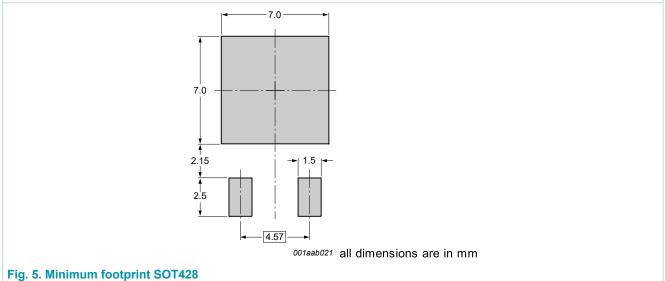
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### 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint; <u>Fig. 5</u>	-	75	-	K/W







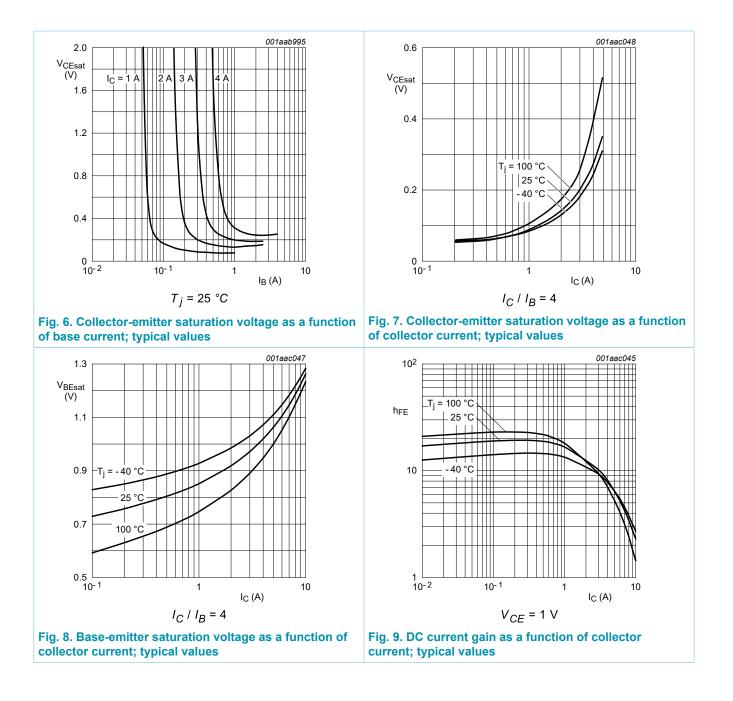
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## 8. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics						
I <sub>CES</sub>	collector-emitter cut-off	$V_{BE}$ = 0 V; $V_{CE}$ = 700 V; $T_j$ = 25 °C	[1]	-	-	0.2	mA
	current (base shorted)	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 125 °C	[1]	-	-	0.5	mA
I <sub>СВО</sub>	collector-base cut-off current (emitter open)	V <sub>CB</sub> = 700 V; I <sub>E</sub> = 0 A	[1]	-	-	0.2	mA
CEO	collector-emitter cut-off current (base open)	V <sub>CE</sub> = 400 V; I <sub>B</sub> = 0 A	[1]	-	-	0.1	mA
ЕВО	emitter-base cut-off current (collector open)	V <sub>EB</sub> = 9 V; I <sub>C</sub> = 0 A		-	-	10	mA
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 4 A; I <sub>B</sub> = 0.8 A; <u>Fig. 6; Fig. 7</u>		-	0.35	1	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 4 A; I <sub>B</sub> = 0.8 A; <u>Fig. 8</u>		-	1	1.5	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 4 A; T <sub>j</sub> = 25 °C		-	1.07	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 4 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 9;</u> <u>Fig. 10</u>		8	12.5	-	
		I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C		10	17	34	
		$I_{C}$ = 500 mA; $V_{CE}$ = 5 V; $T_{mb}$ = 25 °C		13	22	36	
Dynamic ch	aracteristics						
on	turn-on time	$    I_C = 5 \text{ A}; I_{Bon} = 1 \text{ A}; I_{Boff} = -1 \text{ A};     R_L = 75 \Omega; T_j = 25 °C; resistive load;     Fig. 11; Fig. 12                                   $		-	0.65	1	μs
t <sub>s</sub>	storage time			-	1.8	2.5	μs
		$    I_C = 5 \text{ A}; I_{Bon} = 1 \text{ A}; V_{BB} = -5 \text{ V};                                   $		-	1.2	1.7	μs
		$    I_{C} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; V_{BB} = -5 \text{ V}; \\    L_{B} = 1  \mu\text{H}; T_{j} = 100 ^{\circ}\text{C}; \text{ inductive load}; \\    Fig. 13; Fig. 14 $		-	1.4	1.9	μs
t <sub>f</sub>	fall time	$    I_{C} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; V_{BB} = -5 \text{ V};     L_{B} = 1 \mu\text{H}; T_{mb} = 25 \text{ °C}; \text{ inductive load};     Fig. 13; Fig. 14                                   $		-	0.02	0.05	μs
		$I_{C} = 5 \text{ A}; I_{Bon} = 1 \text{ A}; V_{BB} = -5 \text{ V};$ $L_{B} = 1 \mu\text{H}; T_{mb} = 100 ^{\circ}\text{C}; \text{ inductive}$ load; Fig. 13; Fig. 14		-	0.025	0.1	μs
		$I_{C}$ = 5 A; $I_{Bon}$ = 1 A; $I_{Boff}$ = -1 A; R <sub>L</sub> = 75 Ω; resistive load; <u>Fig. 11</u> ; Fig. 12		-	0.3	0.5	μs

[1] Measured with half-sine wave voltage (curve tracer).

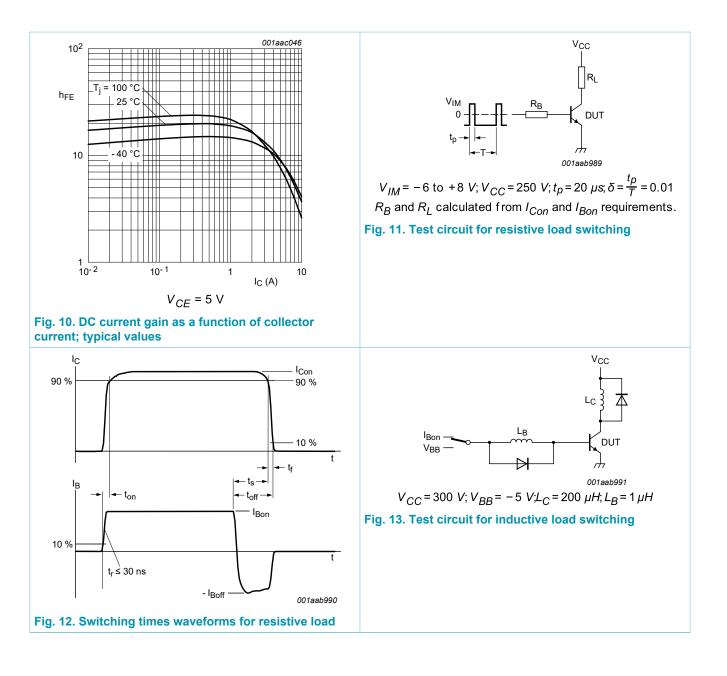
### NPN power transistor with integrated diode



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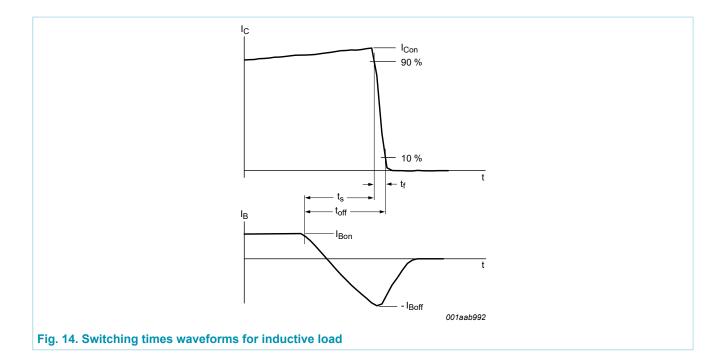
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### 9. Package outline

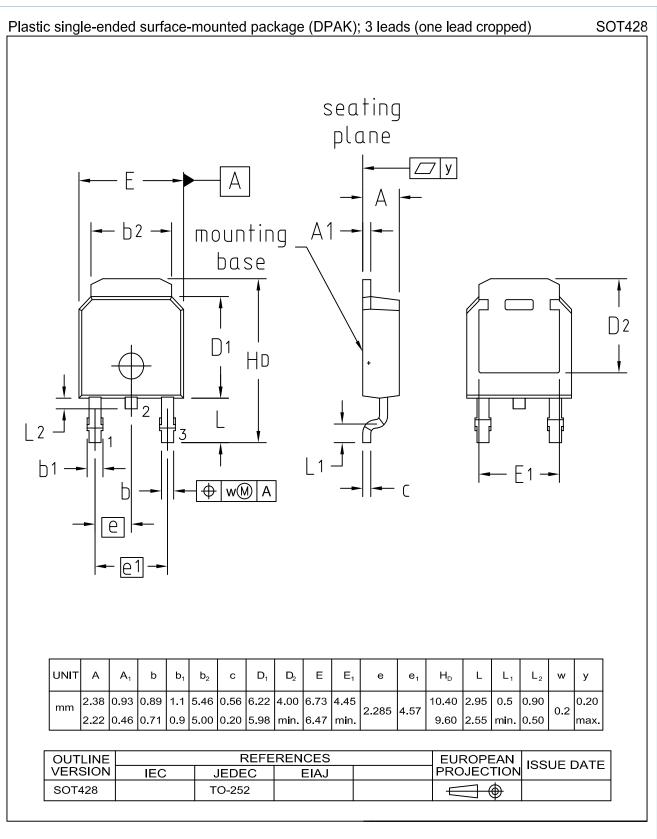


Fig. 15. Package outline DPAK (SOT428)
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#### NPN power transistor with integrated diode

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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